# High Speed Optocoupler, 5 MBd, in SOIC-8 Package

Features

- Data Rate 5.0 Mb/s (2.5 Mb/s over Temperature)
- Buffer
- Isolation Test Voltage, 3000 V_{RMS} for 1.0 s
- TTL, LSTTL and CMOS Compatible
- Internal Shield for Very High Common Mode Transient Immunity
- Wide Supply Voltage Range (4.5 to 15 V)
- Low Input Current (1.6 mA to 5.0 mA)
- Specified from 0 °C to 85 °C
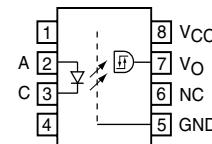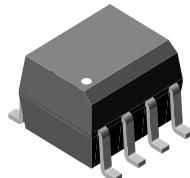
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Agency Approvals

- UL - File No. E52744 System Code Y
- DIN EN 60747-5-2(VDE0884)
  DIN EN 60747-5-5 pending
  Available with Option 1

Applications

Industrial Control

Replace Pulse Transformers

Routine Logic Interfacing

Motion/Power Control

High Speed Line Receiver

Microprocessor System Interfaces

Computer Peripheral Interfaces

Description

The single channel 5.0 Mb/s SFH6720T and SFH6721T high speed optocoupler consists of a GaAlAs infrared emitting diode, optically coupled with an integrated photo detector. The detector incorporates a Schmitt-Trigger stage for improved noise immunity. A Faraday shield provides a common mode

transient immunity of 1000 V/µs at V_{CM} = 50 V for SFH6720T and 2500 V/µs at V_{CM} = 400 V for SFH6721T.

The SFH6720T and SFH6721T uses an industry standard SOIC-8A package.

Order Information

Part	Remarks
SFH6720T	$\mid CM_H \mid$ > 1000, @ $\mid V_{CM} \mid$ = 50 V, SOIC-8
SFH6721T	$\mid CM_H \mid$ > 2500, @ $\mid V_{CM} \mid$ = 400 V, SOIC-8

For additional information on the available options refer to Option Information.

Note Available only on tape and reel.

Truth Table (Positive Logic)

Partnumber	IR Diode	Output
SFH6720T	on	H
	off	L
SFH6721T	on	H
	off	L

SFH6720T/ SFH6721T

Vishay Semiconductors

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	3.0	V
DC Forward current		I_F	10	mA
Surge forward	$t_p \le 1.0$ μs, 300 pulses/s	I_{FSM}	1.0	A
Power dissipation		P_{diss}	20	mW

Output

Parameter	Test condition	Symbol	Value	Unit
Supply voltage		V_{CC}	- 0.5 to + 15	V
Output voltage		V_O	- 0.5 to + 15	V
Average output current		I_O	25	mA
Power dissipation		P_{diss}	100	mW

Coupler

Parameter	Test condition	Symbol	Value	Unit
Storage temperature range		T_{stg}	- 55 to + 125	°C
Ambient temperature range		T_{amb}	- 40 to + 100	°C
Lead soldering temperature	t = 10 s	T_{sld}	260	°C
Isolation test voltage	t = 1.0 s	V_{ISO}	3000	V_{RMS}
Pollution degree			2	
Creepage distance and clearance			4.0	mm
Comparative tracking index per DIN IEC112/VDE 0303, part 1			175	
Isolation resistance	V_{IO} = 500 V, T_{amb} = 25 °C	R_{IO}	10^{12}	Ω
	V_{IO} = 500 V, T_{amb} = 100 °C	R_{IO}	10^{11}	Ω

Recommended Operating Conditions

A 0.1 μF bypass capacitor connected between pins 5 and 8 must be used.

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Supply voltage		V_{CC}	4.5		15	V
Forward input current		I_{Fon}	1.6 [1]		5.0	mA
		I_{Foff}			0.1	mA
Operating temperature		T_A	- 40		85	°C

[1] We recommended using a 2.2 mA if to permit at least 20 % CTR degradation guard band.

Electrical Characteristics

$T_{amb} = 25\ °C$, unless otherwise specified
Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

- 40 °C $\leq T_{amb} \leq$ 85 °C; 4.5 V $\leq V_{CC} \leq$ 15 V; 1.6 mA $\leq I_{Fon} \leq$ 5.0 mA; 2.0 $\leq V_{EH} \leq$ 15 V; 0 $\leq V_{EL} \leq$ 0.8 V; 0 mA $\leq I_{Foff} \leq$ 0.1 mA
Typical values: T_{amb} = 25 °C; V_{CC} = 5.0 V; I_{Fon} = 3.0 mA unless otherwise specified.

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 5.0 mA	V_F		1.6	1.75	V
		V_F			1.9	V
Input current hysteresis	V_{CC} = 5.0 V, I_{HYS} = I_{Fon}-I_{Foff}	I_{HYS}	0.1			V
Reverse current	V_R = 3.0 V	I_R		0.5	10	µA
Capacitance	V_R = 0 V, f = 1.0 MHz	C_O		60		pF
Thermal resistance		R_{thja}		700		K/W

Output

- 40 °C $\leq T_{amb} \leq$ 85 °C; 4.5 V $\leq V_{CC} \leq$ 15 V; 1.6 mA $\leq I_{Fon} \leq$ 5.0 mA; 2.0 $\leq V_{EH} \leq$ 15 V; 0 $\leq V_{EL} \leq$ 0.8 V; 0 mA $\leq I_{Foff} \leq$ 0.1 mA
Typical values: T_{amb} = 25 °C; V_{CC} = 5.0 V; I_{Fon} = 3 .0 mA unless otherwise specified.

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Logic low output voltage	I_{OL} = 6.4 mA	V_{OL}			0.5	V
Logic high output voltage	I_{OH} = - 2.6 mA, * V_{OH} = V_{CC} - 1.8 V	V_{OH}	2.4			V
Output leakage current ($V_{UT}>V_{CC}$)	V_O = 5.5 V, V_{CC} = 4.5 V, I_F = 5.0 mA	I_{OHH}		0.5	100	µA
Output leakage current ($V_{OUT}>V_{CC}$)	V_O = 15 V, V_{CC} = 4.5 V, I_F = 5.0 mA	I_{OHH}		1.0	500	µA
Logic low supply current	V_{CC} = 5.5 V, I_F = 0	I_{CCL}		3.7	6.0	mA
	V_{CC} = 15 V, $I_{=0}$	I_{CCL}		4.1	6.5	mA
Logic high supply current	V_{CC} = 5.5 V, I_F = 5.0 mA	I_{CCH}		3.4	4.0	mA
	V_{CC} = 15 V, I_F = 5.0 mA	I_{CCH}		3.7	5.0	mA
Logic low short circuit output current (output short circuit time ≤10 ms)	V_O = V_{CC} = 5.5 V, I_F = 0	I_{OSL}	25			mA
	V_O = V_{CC} = 15 V, I_F = 0	I_{OSL}	40			mA
Logic high short circuit output current (output short circuit time ≤10 ms)	V_{CC} = 5.5 V, V_O = 0 V, I_F = 5.0 mA	I_{OSH}			- 10	mA
	V_{CC} = 15 V, V_O = 0 V, I_F = 5.0 mA	I_{OSH}			- 25	mA
Thermal resistance		R_{thja}		300		K/W

Coupler

-40 ° C$\leq T_{amb} \leq$ 85 °C; 4.5 V $\leq V_{CC} \leq$ 15 V; 1.6 mA $\leq I_{Fon} \leq$ 5.0 mA; 2.0 $\leq V_{EH} \leq$ 15 V; 0 $\leq V_{EL} \leq$ 0.8 V; 0 mA $\leq I_{Foff} \leq$ 0.1 mA
Typical values: T_{amb} = 25 °C; V_{CC} = 5.0 V; I_{Fon} = 3.0 mA unless otherwise specified.

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Capacitance (input-output)	f = 1.0 MHz, pins 1-4 and 5-8 shorted together	C_{IO}		0.6		pF
Isolation resistance	V_{IO} = 500 V, T_{amb} = 25 °C		10^{12}			Ω
	V_{IO} = 500 V, T_{amb} = 100 °C		10^{11}			Ω
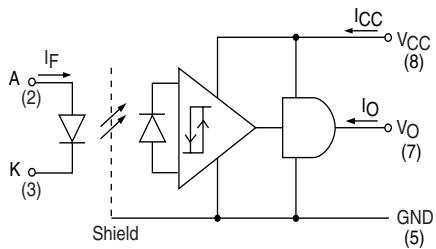
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Switching Characteristics

0 ° C $\leq$ T_{amb} $\leq$ 85 °C; 4.5 V $\leq$ V_{CC} $\leq$ 15 V; 1.6 mA $\leq$ I_{Fon} $\leq$ 5.0 mA; 0 mA $\leq$ I_{Foff} $\leq$ 0.1 mA
Typical values: T_{amb} = 25 ° C; V_{CC} = 5.0 V; I_{Fon} = 3.0 mA unless otherwise specified. [3]

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Propagation delay time to logic low output level	Without peaking capacitor	t_{PHL}		120		ns
	With peaking capacitor	t_{PHL}		115	300	ns
Propagation delay time to logic high output level	Without peaking capacitor	t_{PLH}		125		ns
	With peaking capacitor	t_{PLH}		90	300	ns
Output rise time	10 % to 90 %	t_r		40		ns
Output fall time	90 % to 10 %	t_r		10		ns

(3) A 0.1 µF bypass capacitor connected between pins 5 and 8 must be used

Common Mode Transient Immunity

T_{amb} = 25 °, V_{CC} = 5.0 V, [4]

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Logic High Common Mode Transient Immunity[4]	I V_{CM} I = 50 V, I_F = 1.6 mA	SFH6720T	I CM_HI	1000			V/µs
	I V_{CM} I = 400 V, I_F = 1.6 mA	SFH6721T	I CM_HI	2500			V/µs
Logic Low Common Mode Transient Immunity[4]	I V_{CM} I = 50 V, I_F = 0 mA	SFH6720T	I CM_LI	1000			V/µs
	I V_{CM} I = 400 V, I_F = 0 mA	SFH6721T	I CM_LI	2500			V/µs

[4] CM_H is the maximum slew rate of a common mode voltage V_{CM} at which the output voltage remains at logic high level (V_O > 2.0 V)

CM_L is the maximum slew rate of a common mode voltage V_{CM} at which the output voltage remains at logic high level (V_O < 0.8 V)

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)
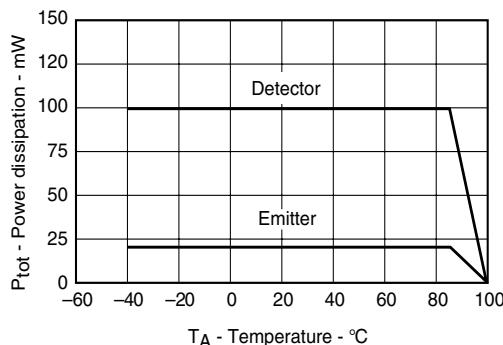
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Fig. 1 Permissible Total Power Dissipation vs. Temperature

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Fig. 2 Typical Input Diode Forward Current vs. Forward Voltage


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Fig. 3 Typical Forward Input Voltage vs. Temperature

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Fig. 4 Typical Output Voltage vs. Forward Input Current


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Fig. 5 Typical Supply Current vs. Temperature
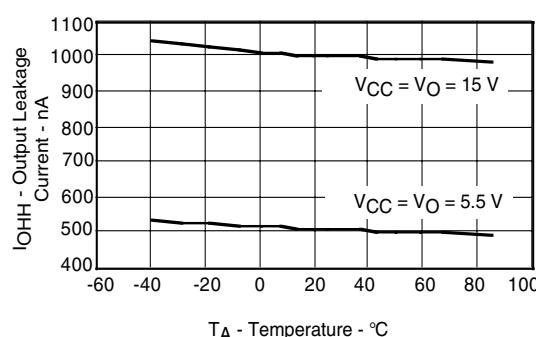
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Fig. 6 Typical Output Leakage Current vs. Temperature
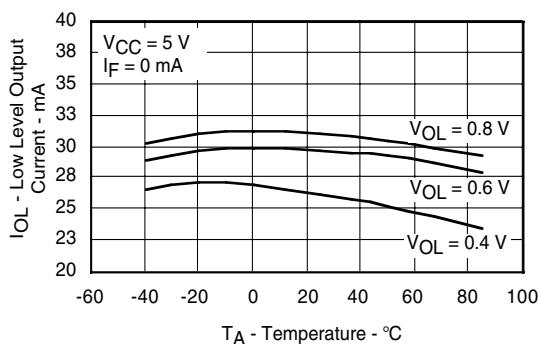
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Fig. 7   Typical Low Level Output Current vs. Temperature

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Fig. 8   Typical Low Level Output Voltage vs. Temperature

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Fig. 9   Typical High Level Output Current vs. Temperature
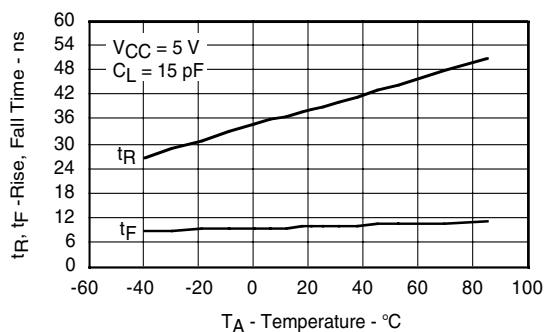
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Fig. 10 Typical Rise, Fall Time vs. Temperature
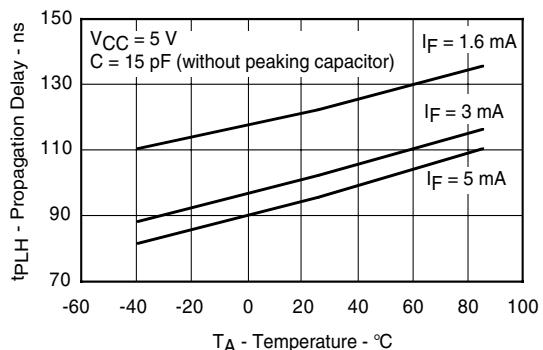
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Fig. 11 Typical Propagation Delays to Logic High vs. Temperature
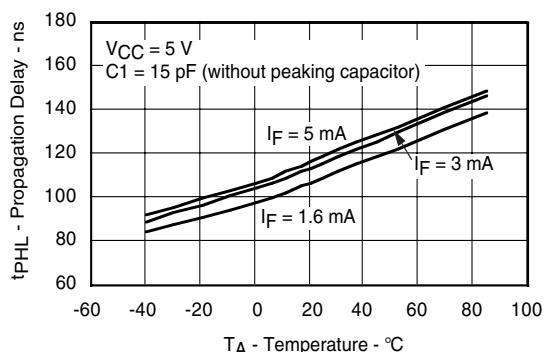
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Fig. 12 Typical Propagation Delays to Logic Low vs.Temperature
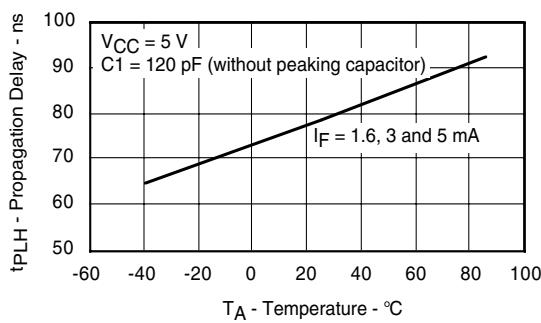
Fig. 13 Typical Propagation Delays to Logic High vs. Temperature
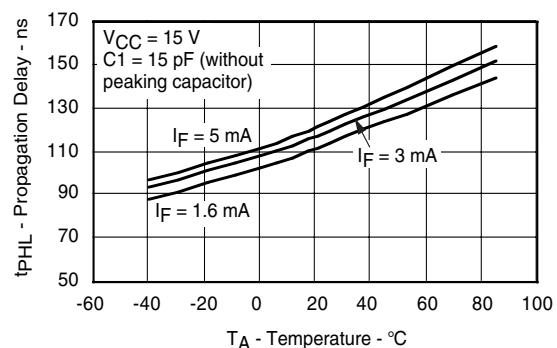
Fig. 16 Typical Propagation Delays to Logic Low vs.Temperature
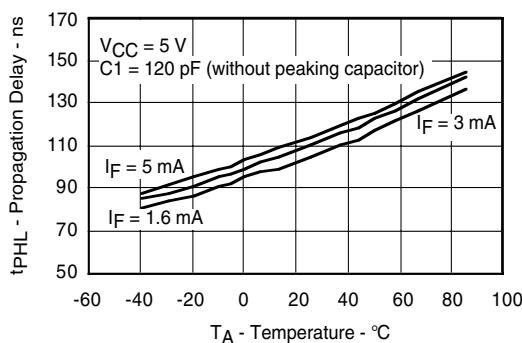
Fig. 14 Typical Propagation Delays to Logic Low vs.Temperature
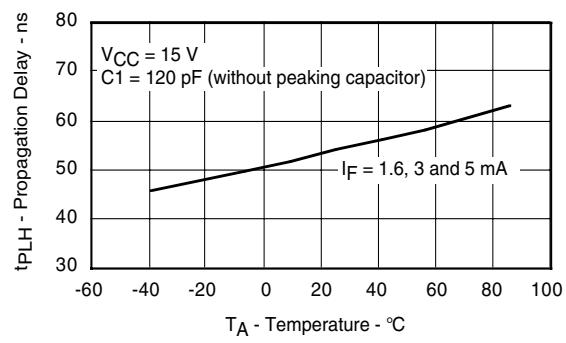
Fig. 17 Typical Propagation Delays to Logic High vs. Temperature
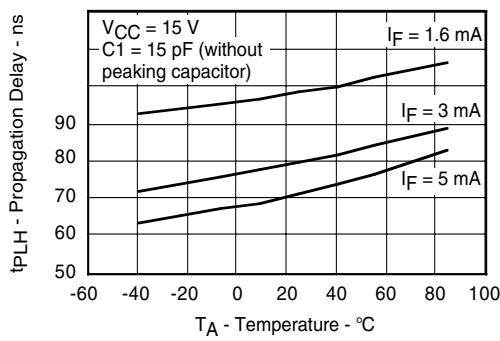
Fig. 15 Typical Propagation Delays to Logic High vs. Temperature
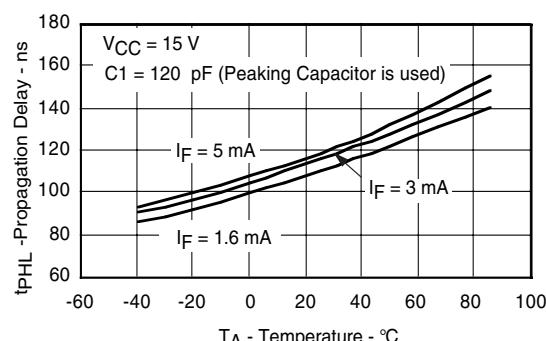
Fig. 18 Typical Propagation Delays to Logic Low vs.Temperature
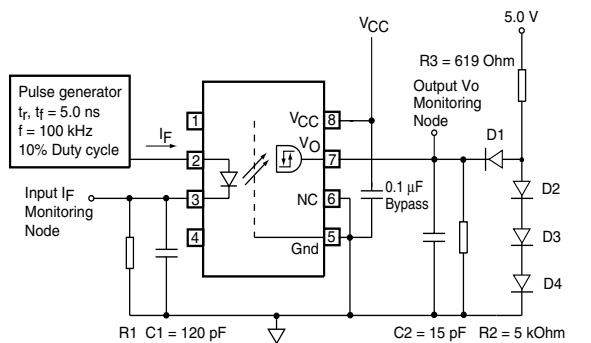
The Probe and Jig Capacitances are included in C1 and C2

All diodes are 1N916 or 1N3064

| R1	2.15 kΩ	1.1 kΩ	681 Ω
I_F (ON)	1.6 mA	3 mA	5 mA
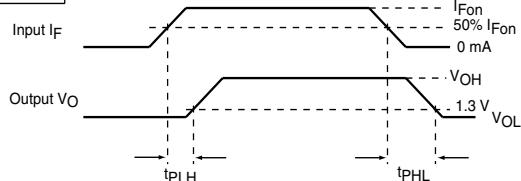
Fig. 19 Test Circuit for t_{PLH}, t_{PHL}, t_r and t_f
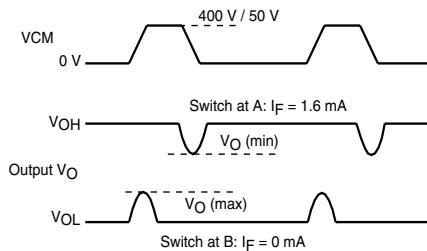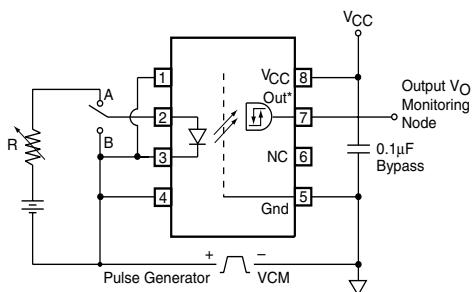
Fig. 20 Test Circuit for Common Mode Transient Immunity and Typical Waveforms

Package Dimensions in Inches (mm)

ISO Method A
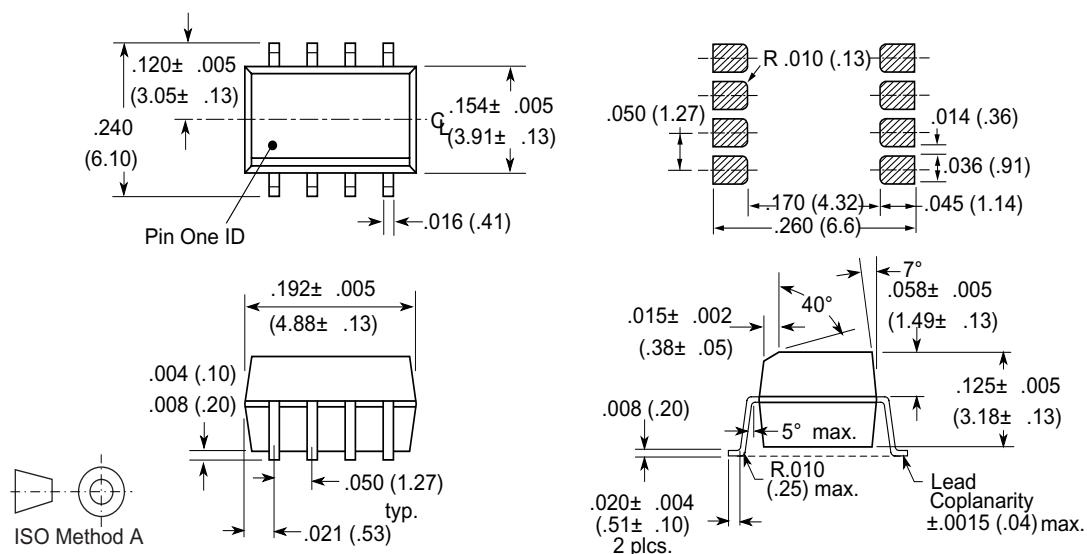
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Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively

2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA

3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.